

SOT23 N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

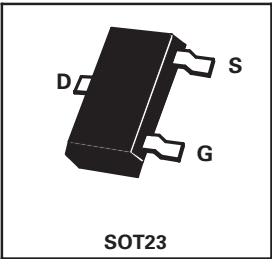
ZVN3310F

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FEATURES

- * 100 Volt V_{DS}
- * $R_{DS(on)} = 10\Omega$

COMPLEMENTARY TYPE - ZVP3310F
PARTMARKING DETAIL - MF



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	V_{DS}	100	V
Continuous Drain Current at $T_{amb}=25^{\circ}C$	I_D	100	mA
Pulsed Drain Current	I_{DM}	2	A
Gate-Source Voltage	V_{GS}	± 20	V
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	330	mW
Operating and Storage Temperature Range	$T_j:T_{stg}$	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	BV_{DSS}	100		V	$I_D = 1mA, V_{GS} = 0V$
Gate-Source Threshold Voltage	$V_{GS(th)}$	0.8	2.4	V	$I_D = 1mA, V_{DS} = V_{GS}$
Gate-Body Leakage	I_{GSS}		20	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
Zero Gate Voltage Drain Current	I_{DSS}		1 50	μA μA	$V_{DS} = 100V, V_{GS} = 0$ $V_{DS} = 80V, V_{GS} = 0V, T = 125^{\circ}C(2)$
On-State Drain Current(1)	$I_{D(on)}$	500		mA	$V_{DS} = 25V, V_{GS} = 10V$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$		10	Ω	$V_{GS} = 10V, I_D = 500mA$
Forward Transconductance (1)(2)	g_{fs}	100		mS	$V_{DS} = 25V, I_D = 500mA$
Input Capacitance (2)	C_{iss}		40	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1MHz$
Common Source Output Capacitance (2)	C_{oss}		15	pF	
Reverse Transfer Capacitance (2)	C_{rss}		5	pF	
Turn-On Delay Time (2)(3)	$t_{d(on)}$	3 typ	5	ns	$V_{DD} = 25V, I_D = 500mA$
Rise Time (2)(3)	t_r	5 typ	7	ns	
Turn-Off Delay Time (2)(3)	$t_{d(off)}$	4 typ	6	ns	
Fall Time (2)(3)	t_f	5 typ	7	ns	

(1) Measured under pulsed conditions. Width=300 μs . Duty cycle $\leq 2\%$ (2) Sample test.
(3) Switching times measured with 50 Ω source impedance and <5ns rise time on a pulse generator

TYPICAL CHARACTERISTICS

